

2N50

DESCRIPTION

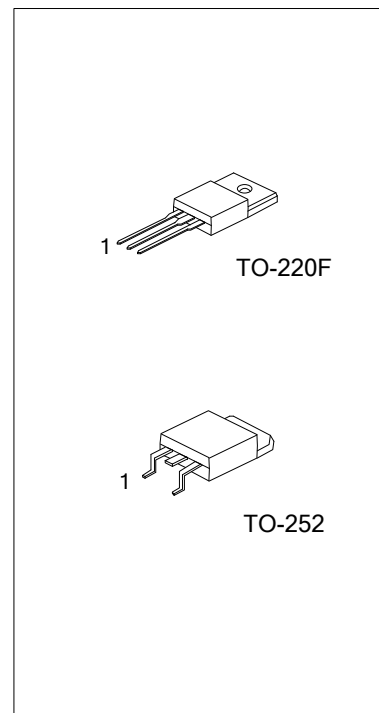
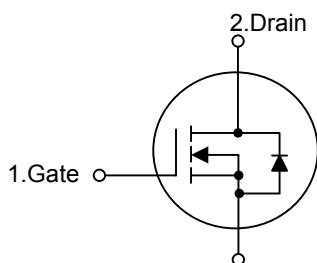
The **2N50** is an N-channel mode power MOSFET using advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The **2N50** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.

FEATURES

- * $R_{DS(ON)} = 4.9\Omega @ V_{GS}=10V$
- * High Switching Speed
- * 100% Avalanche Tested

SYMBOL



ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous ($T_C=25^\circ\text{C}$)	I_D	2 (Note 3)	A
	Pulsed (Note 2)	I_{DM}	8 (Note 3)	A
Avalanche Current (Note 2)		I_{AR}	2	A
Avalanche Energy	Single Pulsed	E_{AS}	82	mJ
	Repetitive (Note 4)	E_{AR}	3.3	mJ
Power Dissipation ($T_C=25^\circ\text{C}$)	TO-220F	P_D	23	W
	TO-252		50	
Derate above 25°C	TO-220F		0.18	$W/^\circ\text{C}$
	TO-252		0.4	
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. Drain current limited by maximum junction temperature

4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-252		110	
Junction to Case	TO-220F	θ_{JC}	5.5	$^\circ\text{C/W}$
	TO-252		2.5	



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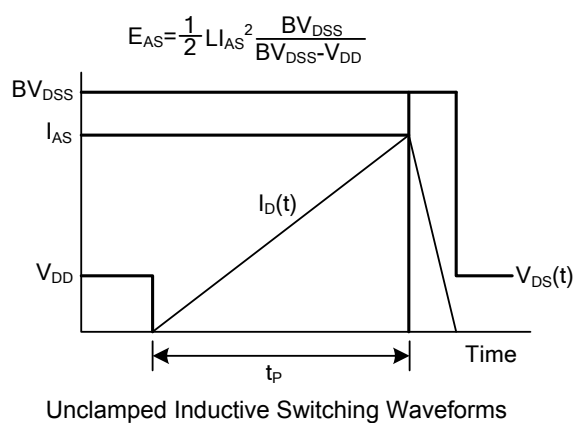
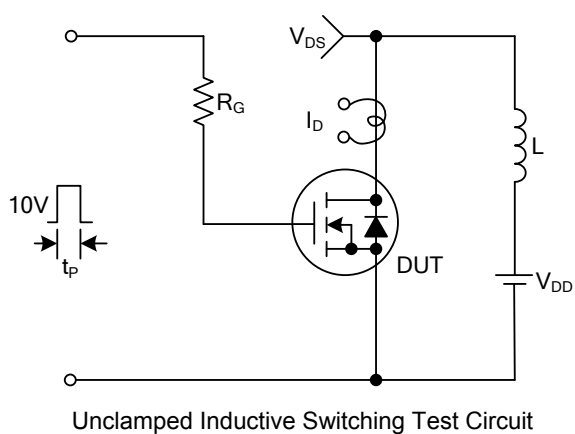
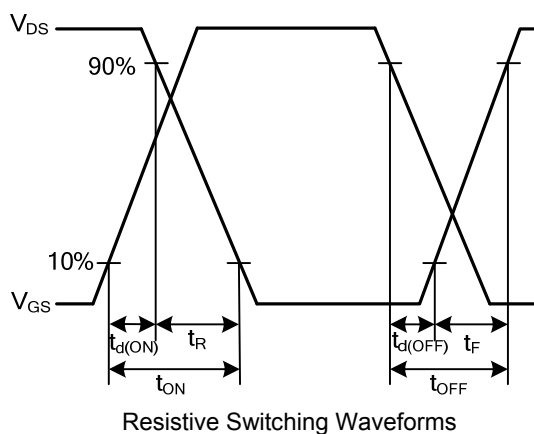
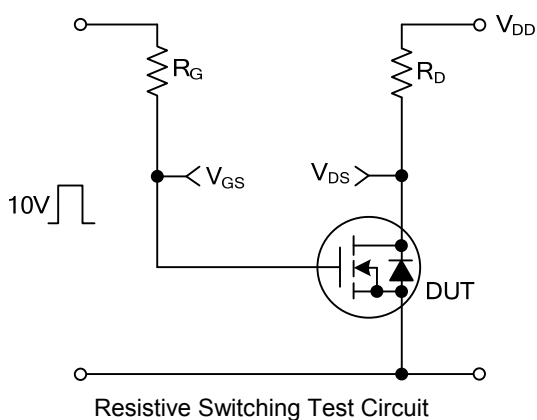
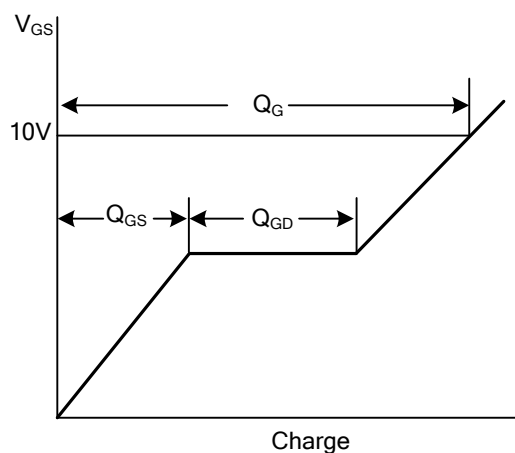
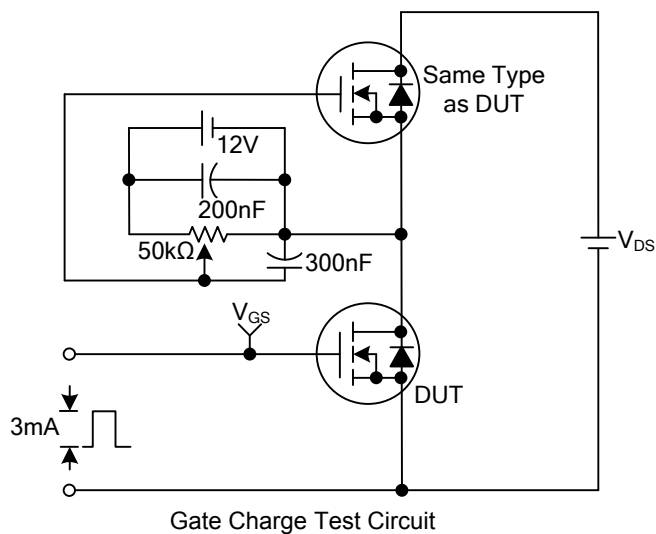
■ ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	500			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =500V, V _{GS} =0V			25	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =1A		3.9	4.9	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		236		pF
Output Capacitance		C _{OSS}			40		pF
Reverse Transfer Capacitance		C _{RSS}			22		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q _G	V _{GS} =10V, V _{DS} =400V, I _D =2A (Note 1, 2)		20	25	nC
Gate to Source Charge		Q _{GS}			2	3	nC
Gate to Drain Charge		Q _{GD}			12	15	nC
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =250V, I _D =2A, R _G =25Ω (Note 1, 2)		10		ns
Rise Time		t _R			20		ns
Turn-OFF Delay Time		t _{D(OFF)}			60		ns
Fall-Time		t _F			20		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				2	A
Maximum Body-Diode Pulsed Current		I _{SM}				8	A
Drain-Source Diode Forward Voltage		V _{SD}	I _S =2A, V _{GS} =0V			1.2	V
Body Diode Reverse Recovery Time		t _{RR}	I _S =2A, V _{GS} =0V, dI _F /dt=100A/μs		300		ns
Body Diode Reverse Recovery Charge		Q _{RR}	(Note 1)		2.1		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature

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■ TEST CIRCUITS AND WAVEFORMS



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■ TEST CIRCUITS AND WAVEFORMS(Cont.)

